

Description

The Si2306BDS-T1-GE3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOT-23

General Features

 $V_{DS} = 30V I_D = 4A$

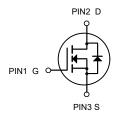
 $R_{DS(ON)}$ < 38m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
Si2306BDS-T1-GE3	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25 [°]C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	4	А
Ім	Drain Current-Pulsed (Note 1)	16.4	А
P _D	Maximum Power Dissipation	1	W
Тл,Твтв	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	125	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μΑ	
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.5	2.5	V	
	Static Drain-Source on-Resistance	V _{GS} =10V, I _D =4A	-	29	38	mQ	
$R_{DS(on)}$		V_{GS} =4.5V, I_D =3A	-	45	65	11177	
C_{iss}	Input Capacitance	\/ -45\/ \/ -0\/	-	233	_	pF	
Coss	Output Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	44	-	pF	
C _{rss}	Reverse Transfer Capacitance	1-1.UIVITZ	-	33	-	pF	
Qg	Total Gate Charge	V _{DS} =15V, I _D =2A,	-	3	-	nC	
Q _{gs}	Gate-Source Charge		-	0.5	-	nC	
Q_{gd}	Gate-Drain("Miller") Charge	V _{GS} =10V	-	0.8	-	nC	
t _{d(on)}	Turn-on Delay Time	V_{DS} =15 V , I_{D} =4 A , R_{GEN} =3 Ω ,	-	4	-	ns	
t _r	Turn-on Rise Time		-	2.1	-	ns	
t _{d(off)}	Turn-off Delay Time		-	15	-	ns	
t _f	Turn-off Fall Time	- V _{GS} =10V	-	3.2	-	ns	
Is	Maximum Continuous Drain to Source Diode Forward Current		_	_	4	Α	
IS			_	-	4		
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	Α	
V_{SD}	Drain to Source Diode Forward Voltage V _{GS} =0V, I _S =4A		-	-	1.2	V	

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

^{2.} Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



Typical Characteristics

Figure1: Output Characteristics

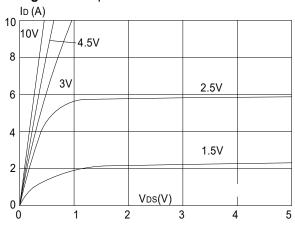


Figure 2: Typical Transfer Characteristics

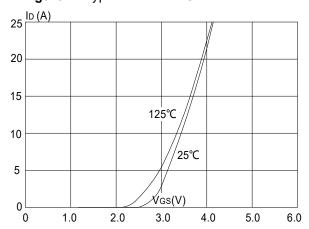


Figure 3:On-resistance vs. Drain Current

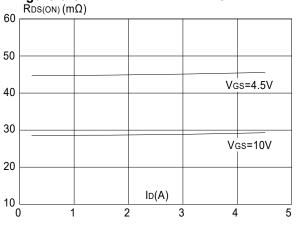


Figure 4: Body Diode Characteristics

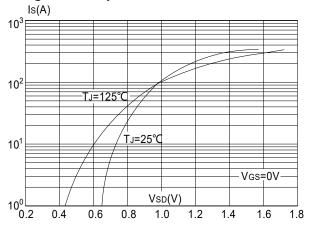


Figure 5: Gate Charge Characteristics

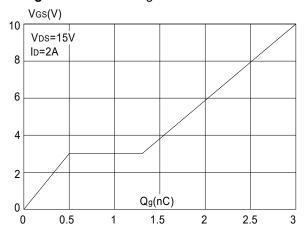


Figure 6: Capacitance Characteristics

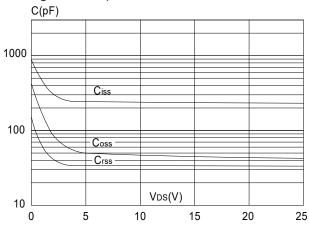




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

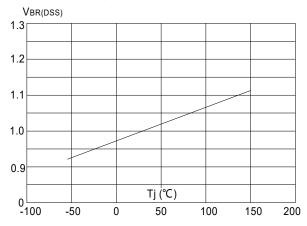


Figure 8: Normalized on Resistance vs. Junction Temperature

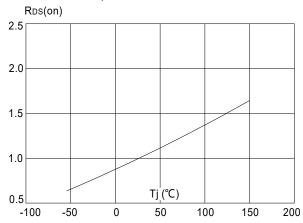


Figure 9: Maximum Safe Operating Area

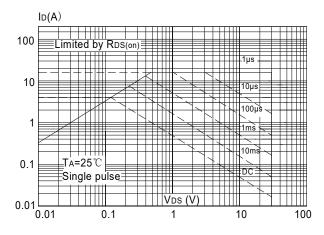


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

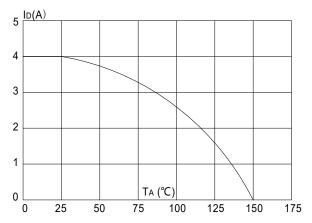
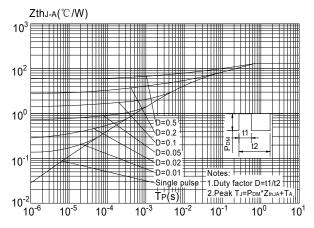
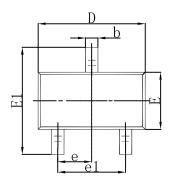


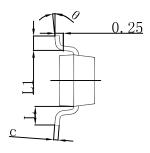
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

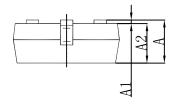




SOT-23 Package Outline Dimensions

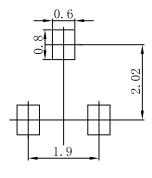






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

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